

## R-C Thermal Model Parameters

### DESCRIPTION

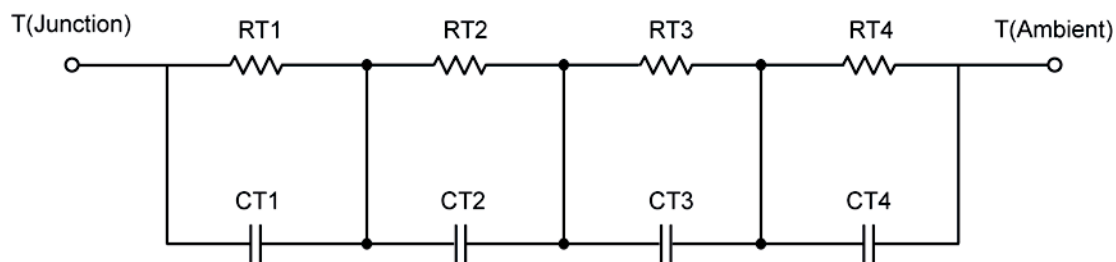
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

*Note:*

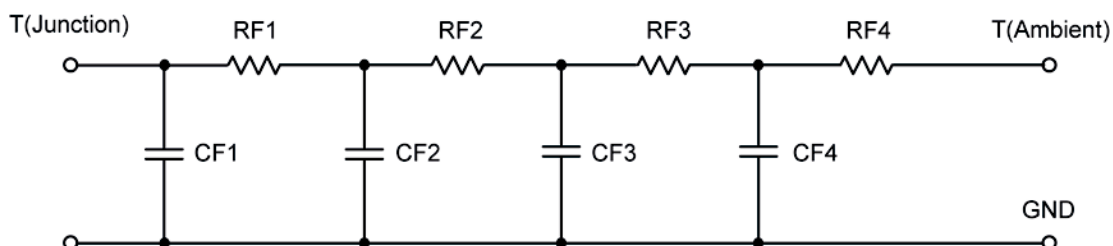
*For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).*

### R-C THERMAL MODEL FOR TANK CONFIGURATION



<b>R-C VALUES FOR TANK CONFIGURATION</b>			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	8.1299	N/A	3.8547
RT2	32.5344	N/A	26.5144
RT3	25.1850	N/A	17.6050
RT4	54.1507	N/A	8.0259
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	4.6246 m	N/A	4.8650 m
CT2	43.0454 m	N/A	25.9783 m
CT3	31.0009 m	N/A	108.9077 m
CT4	1.6502	N/A	16.9808 m

*This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.*

**R-C THERMAL MODEL FOR FILTER CONFIGURATION****R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RF1	8.9573	N/A	4.3113
RF2	30.3009	N/A	15.1162
RF3	28.6967	N/A	22.5419
RF4	52.0451	N/A	14.0306
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CF1	3.0917 m	N/A	2.2216 m
CF2	11.1350 m	N/A	5.5913 m
CF3	17.9191 m	N/A	12.5639 m
CF4	1.7371	N/A	52.9238 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

